

NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SRF 1136** is a Common Emitter Device Designed for class C Amplifier Applications up to 1 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	800 mA
V_{CB0}	36 V
P_{DISS}	19 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	7.5 °C/W

PACKAGE STYLE 280 4L STUDLESS

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/2/14.53	
G	.130/3.30	
H	.275/6.99	.285/7.24
I	.640/16.26	
J	.175/4.45	.21/75.51

1 = Collector 3 = Base
 2 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 10 mA	36			V
BV_{CEO}	I _C = 20 mA	16			V
BV_{EBO}	I _E = 1 mA	3.0			V
h_{FE}	V _{CE} = 10 V I _C = 600 mA	25	100		---
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz		5		pF
*P_G					dB
*η_C					%

* RF SPECIFICATIONS ARE CONTROLLED BY CUSTOMER DRAWING AND ARE PROPRIETARY.